

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

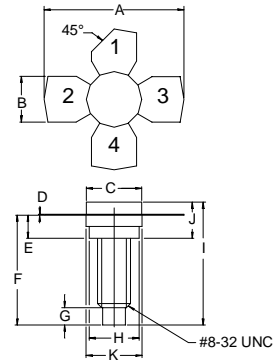
The **ASI MRF587** is Designed for High Linearity Power Amplifier Applications up to 500 MHz.

FEATURES:

- $P_E = 16$ dB Typical at 220 W/500 MHz
- Low Noise Figure
- Diffused Ballast Resistors
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	200 mA
V_{CBO}	34 V
V_{CEO}	17 V
V_{EBO}	2.5 V
P_{DISS}	5.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C

PACKAGE STYLE .280 4L STUD


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

Lead 1 = Collector 2 & 3 = Emitter 4 = Base

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0$ mA	34			V
BV_{CEO}	$I_C = 5.0$ mA	17			V
BV_{EBO}	$I_E = 100$ μ A	2.5			V
I_{CBO}	$V_{CB} = 10$ V			50	μ A
h_{FE}	$V_{CE} = 5.0$ V $I_C = 50$ mA	50		200	---
C_{cb}	$V_{CB} = 10$ V $f = 1.0$ MHz		1.7	2.2	pF
G_P η_C	$V_{CC} = 15$ V $I_C = 90$ mA $f = 0.3$ GHz	11	65		dB %